Application No.: 10/769,787 Docket No.: M4065.0989/P989-A

## **AMENDMENTS TO THE CLAIMS**

- 1-9. (Cancelled)
- 10. (Original) A method of forming memory cells in a programmable conductor random access memory (PCRAM) comprising:
  - (a) forming a plurality of electrodes;
  - (b) forming a layer of chalcogenide glass;
- (c) forming a layer of silver selenide adjacent to the layer of chalcogenide glass;
  - (d) forming a mask pattern over the layer of silver selenide;
  - (e) implanting unmasked portions of the layer of silver selenide with oxygen;
  - (f) removing the mask pattern;
- (g) annealing the layer of implanted silver selenide such that the layer is essentially free of selenium oxide thereby forming silver-rich regions of silver selenide; and
- (h) patterning to define cells, where patterning selectively removes unenriched regions of silver selenide.
- 11. (Original) The method as defined in Claim 10, further comprising repeating (d) to (g) to further increase an amount of silver in the silver-rich regions of silver selenide.
- 12. (Original) The process as defined in Claim 10, further comprising forming electrodes in a cross-point configuration.

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13. (Original) The process as defined in Claim 10, wherein the layer of chalcogenide glass is formed before forming the layer of silver selenide.

- 14. (Original) The process as defined in Claim 10, wherein the layer of chalcogenide glass is formed after forming, implanting, annealing, and patterning the layer of silver selenide.
  - 15. (Cancelled).
- 16. (Currently Amended) The process as defined in Claim 15, wherein removing the selected amount of chalcogenide further comprises: A process to increase a ratio of silver to a chalcogenide material in a composition of silver chalcogenide, comprising:

## providing silver chalcogenide; and

removing a selected amount of chalcogenide from the silver chalcogenide by implanting oxygen <u>in</u>to the silver chalcogenide[[;]] and annealing the oxygen-implanted silver chalcogenide.

- 17. (Original) The process as defined in Claim 16, further comprising repeating implanting and annealing for a predetermined number of times to further increase the ratio of silver to chalcogenide.
- 18. (Original) The process as defined in Claim 16, wherein the silver chalcogenide is selected from the group consisting of silver selenide, silver telluride, and silver sulfide.
- 19. (Original) The process as defined in Claim 16, wherein the silver chalcogenide is silver selenide.